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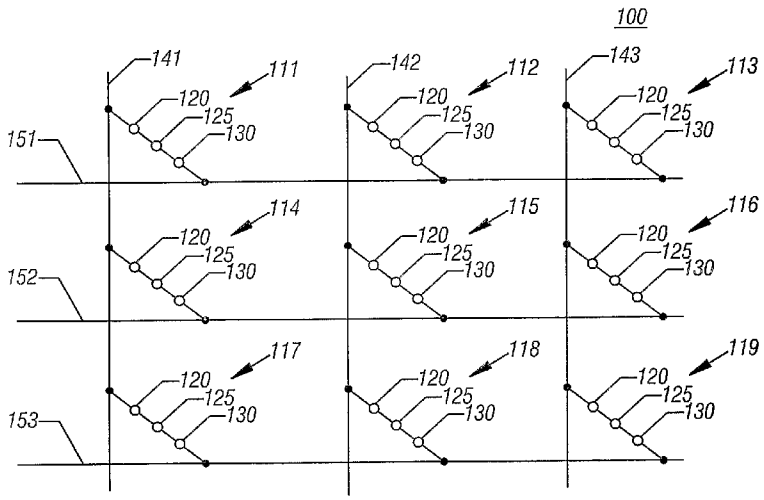
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(54) **Title:** ACCESSING PHASE CHANGE MEMORIES




(57) **Abstract:** A memory (100) may include a phase change memory element (130) and series connected first (125) and second (120) selection devices. The second selection device (120) may have a higher resistance and a larger threshold voltage than the first selection device (125). In one embodiment, the first selection device may have a threshold voltage substantially equal to its holding voltage. In some embodiments, the selection devices (120, 125) and the memory element (130) may be made of chalcogenide. In some embodiments, the selection devices (120, 125) may be made of non-programmable chalcogenide. The selection device with the higher threshold voltage may contribute lower leakage to the combination, but may also exhibit increased snapback. This increased snapback may be counteracted by the selection device with the lower threshold voltage, resulting in a combination with low leakage and high performance in some embodiments.

WO 2006/004677 A1

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